Discrete POWER & Signal **Technologies** 

# 2N5769

2N5769

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SEMICONDUCTOR TM



## **NPN Switching Transistor**

This device is designed for high speed saturated switching applications at currents to 100 mA. Sourced from Process 21. See PN2369A for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	15	V	
V <sub>CBO</sub>	Collector-Base Voltage	40	V	
$V_{\text{EBO}}$	Emitter-Base Voltage	4.5	V	
I <sub>C</sub>	Collector Current - Continuous	200	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		2N5769		
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W	
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	357	°C/W	

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## **NPN Switching Transistor**

0.59

1.02

1.15

1.6

V

V

V

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	15		V
/ <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	40		V
/ <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	4.5		V
/ <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \ \mu A, I_{\rm B} = 0$	40		V
СВО	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$		0.4	μA
		$V_{CB} = 20 \text{ V}, \text{ I}_{E} = 0, \text{ T}_{A} = 125 ^{\circ}\text{C}$		30	μA
CES	Collector Cutoff Current	$V_{CE} = 20 \text{ V}, \text{ I}_{B} = 0$		0.4	μA
EBO	Emitter Cutoff Current	$V_{EB} = 4.5 \text{ V}, I_{C} = 0$		1.0	μA
ON CHAF	RACTERISTICS*	$I_{c} = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $I_{c} = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $T_{A} = -55 \text{ °C}$ $I_{c} = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$ $I_{c} = 100 \text{ mA}, V_{ce} = 1.0 \text{ V}$	40 20 30 20	120	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$\label{eq:loss} \begin{array}{l} I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 1.0 \text{ V} \\ I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA} \\ I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA} \\ T_{\rm A} = 125 \ ^{\circ}\text{C} \\ I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 3.0 \text{ mA} \end{array}$	20	0.2 0.3 0.25	V V V
	Base-Emitter Saturation Voltage	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$ $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$	0.7	0.5 0.85	V V
/ <sub>BE(sat)</sub>	Dase Emilier Galdraiton Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA	0.1	0.00	•

## $h_{\text{FE}}$

C <sub>cb</sub>	Collector-Base Capacitance	$V_{CB} = 5.0 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		4.0	pF
hfe	Small-Signal Current Gain	$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 10 V, f = 100 MHz	5.0		

 $I_{c} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$  $T_{A} = -55 \text{ °C}$ 

 $I_{c} = 30 \text{ mA}, I_{B} = 3.0 \text{ mA}$  $I_{c} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$ 

## SWITCHING CHARACTERISTICS

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 10 mA,	12	ns
t <sub>off</sub>	Turn-off Time	$I_{B1} = 3.0 \text{ mA}, I_{B2} = 1.5 \text{ mA}$	 18	ns
ts	Storage Time	$I_{\rm C} = I_{\rm B1} = I_{\rm B2} = 10 \text{ mA}$	13	ns

\*Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%

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